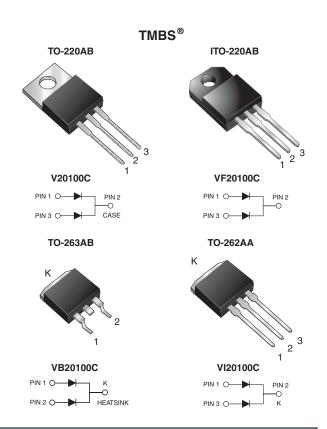


Vishay General Semiconductor

Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.50 \text{ V}$ at $I_F = 5 \text{ A}$



PRIMARY CHARACTERISTICS						
Package	TO-220AB, ITO-220AB, TO-263AB, TO-262AA					
I _{F(AV)}	2 x 10 A					
V _{RRM}	100 V					
I _{FSM}	150 A					
V _F at I _F = 10 A	0.58 V					
T _J max.	150 °C					
Diode variation	Common cathode					

FEATURES





- Low forward voltage drop, low power losses
- · High efficiency operation

- RoHS
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER		SYMBOL	V20100C	VF20100C	VB20100C	VI20100C	UNIT
Maximum repetitive peak reverse voltage		V _{RRM}	100			V	
Mariana and Caranda and Caranda and Caranda	per device		20			A	
Maximum average forward rectified current (fig. 1)	per diode	I _{F(AV)}	10				
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		I _{FSM}	150			Α	
Non-repetitive avalanche energy at T _J = 25 °C, L = 60 mH per diode		E _{AS}	150			mJ	
Peak repetitive reverse current at t_p = 2 μ s, 1 kHz, T_J = 38 °C \pm 2 °C per diode		I _{RRM}	1.0		Α		
Voltage rate of change (rated V _R)		dV/dt	10 000			V/µs	
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min		V _{AC}	1500			V	
Operating junction and storage temperature range		T _J , T _{STG}	- 40 to + 150			°C	

V20100C, VF20100C, VB20100C, VI20100C

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)							
PARAMETER	TEST CO	NDITIONS	SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	I _R = 10 mA	T _A = 25 °C	V_{BR}	105 (minimum)	-	V	
Instantaneous forward voltage per diode	I _F = 5 A	T _A = 25 °C	V _F ⁽¹⁾	0.55	-	V	
	I _F = 10 A			0.65	0.79		
	I _F = 5 A	T _A = 125 °C		0.50	-		
	I _F = 10 A			0.58	0.68		
Reverse current per diode	V _R = 70 V	T _A = 25 °C		17	-	μΑ	
	v _R = 70 v	T _A = 125 °C	1 (2)	5.3	-	mA	
	V - 100 V	T _A = 25 °C	I _R ⁽²⁾	-	800	μΑ	
	$V_R = 100 \text{ V}$ $T_A = 100 \text{ V}$	T _A = 125 °C		12	25	mA	

Notes

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V20100C	VF20100C	VB20100C	VI20100C	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.8	5.5	2.8	2.8	°C/W

ORDERING INFORMATION (Example)								
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE			
TO-220AB	V20100C-E3/4W	1.881	4W	50/tube	Tube			
ITO-220AB	VF20100C-E3/4W	1.75	4W	50/tube	Tube			
TO-263AB	VB20100C-E3/4W	1.39	4W	50/tube	Tube			
TO-263AB	VB20100C-E3/8W	1.39	8W	800/reel	Tape and reel			
TO-262AA	VI20100C-E3/4W	1.452	4W	50/tube	Tube			

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

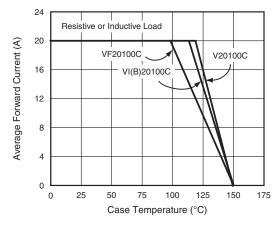


Fig. 1 - Maximum Forward Current Derating Curve

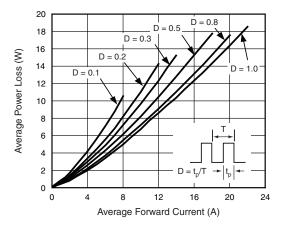


Fig. 2 - Forward Power Loss Characteristics Per Diode





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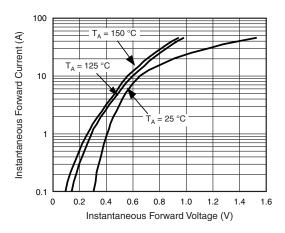


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

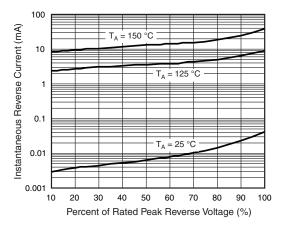


Fig. 4 - Typical Reverse Characteristics Per Diode

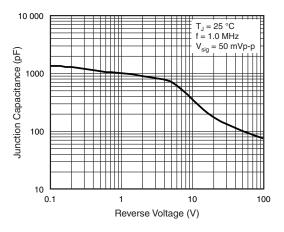


Fig. 5 - Typical Junction Capacitance Per Diode

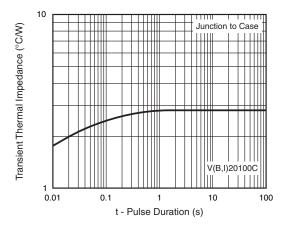


Fig. 6 - Typical Transient Thermal Impedance Per Diode

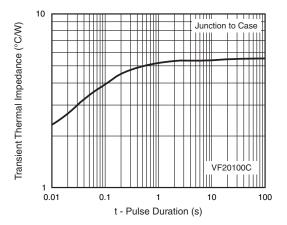
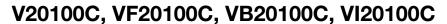


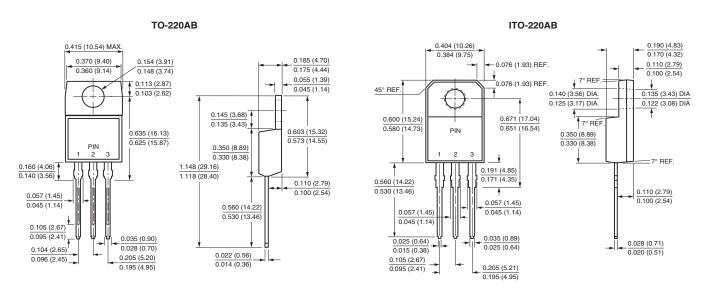
Fig. 7 - Typical Transient Thermal Impedance Per Diode

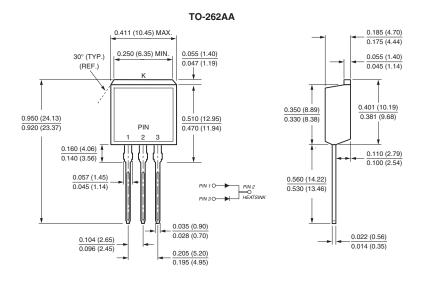


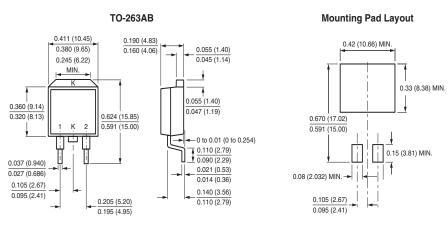


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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)









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